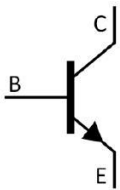


SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

2SA1981S

High h_{FE} , complementary pair with 2SA1981S.

Audio power amplifier application.

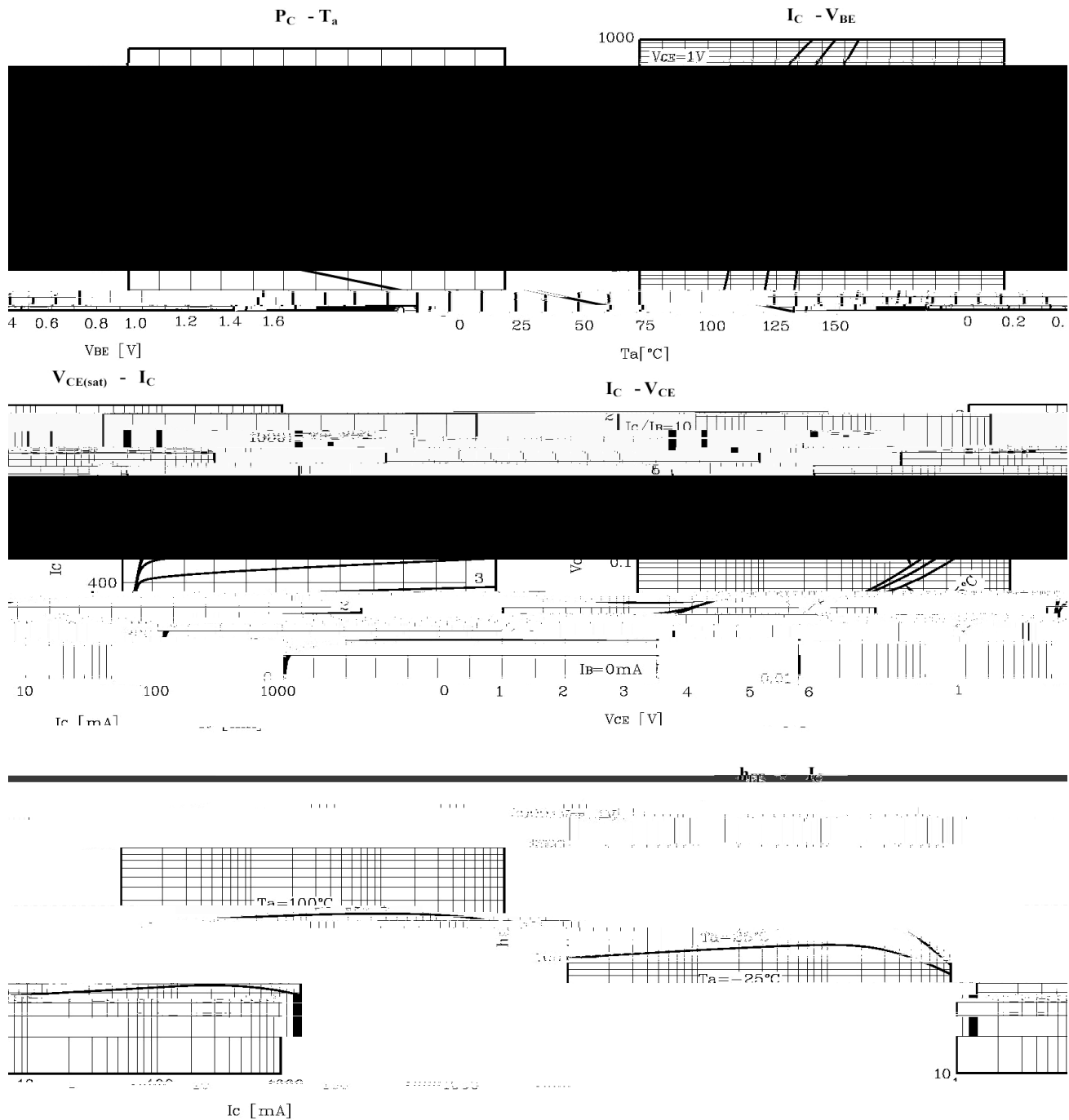


PIN1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HFAO	HFAY

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\text{ A}$ $I_E=0$	35			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0\text{mA}$ $I_B=0$	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\text{ A}$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35\text{V}$ $I_E=0$			0.1	A
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0\text{V}$ $I_C=0$			0.1	A
DC Current Gain	h_{FE}	$V_{CE}=1.0\text{V}$ $I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$ $I_B=50\text{mA}$			0.5	V
Transition Frequency	f_T	$V_{CE}=5.0\text{V}$ $I_C=10\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$ $f=1.0\text{MHz}$ $I_E=0$		13		pF





H

FA

O h_{FE}

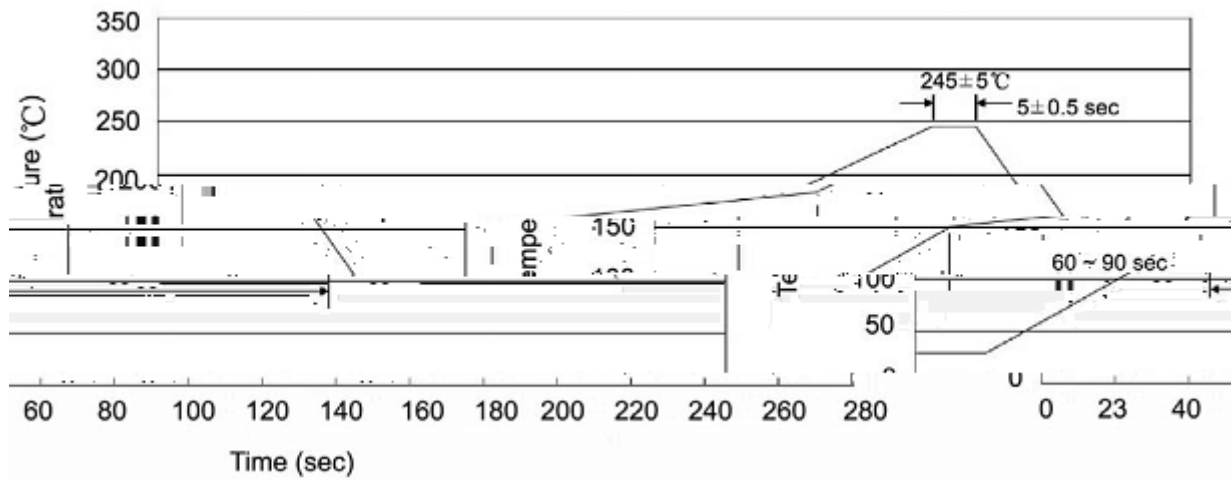
Note:

H Company Code

FA Product Type Code

O h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

2

245±5

5±0.5sec;

3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205